

	<h2>SI4362BDY-T1-E3</h2>
	<p>Hersteller-Teilenummer: SI4362BDY-T1-E3</p> <p>Hersteller / Marke: Electro-Films (EFI) / Vishay</p> <p>Teil der Beschreibung: MOSFET N-CH 30V 29A 8-SOIC</p> <p>Datenblätter:  SI4362BDY-T1-E3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 99280 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SI4362BDY-T1-E3
Hersteller	Electro-Films (EFI) / Vishay
Beschreibung	MOSFET N-CH 30V 29A 8-SOIC
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs ,
Teilstatus	99280 pcs Stock
detaillierte Beschreibung	N-Channel 30V 29A (Tc) 3W (Ta), 6.6W (Tc) Surface
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	8-SOIC (0.154", 3.90mm Width)
Supplier Device-Gehäuse	8-SO
Verlustleistung (max)	3W (Ta), 6.6W (Tc)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	30V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	29A (Tc)
Rds On (Max) @ Id, Vgs	4.6 mOhm @ 19.8A, 10V
VGS (th) (Max) @ Id	2V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	115nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	4800pF @ 15V
Antriebsspannung (Max Rds On, Min Rds On)	4.5V, 10V
Vgs (Max)	±12V
Verpackung	Tape & Reel (TR)
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)

SI4362BDY-T1-E3 ist neu im Original, Suche SI4362BDY-T1-E3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI4362BDY-T1-E3 Electro-Films (EFI) / Vishay mit Garantie und Vertrauen. Anfrage SI4362BDY-T1-E3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SI4362BDY-T1 VISHAY VISHAY SOP8</p>	 <p>SI4362-C2A-GMR Energy Micro (Silicon Labs) IC RCVR EZRADIO SUB GHZ 20QFN</p>	 <p>SI4362DY VISHAY SI4362DY VISHAY</p>	 <p>SI4362BDY-T1-GE3 Vishay / Siliconix MOSFET N-CH 30V 29A 8-SOIC</p>
 <p>SI4362BDY-T1-E3 Vishay / Siliconix MOSFET N-CH 30V 29A 8-SOIC</p>	 <p>SI4362-C2A-GM Energy Micro (Silicon Labs) EZRADIOPRO SUB GHZ RECEIVER, -11</p>	 <p>SI4362BDY-T1-E3-PBF VISHAY SI4362BDY-T1-E3-PBF VISHAY</p>	 <p>SI4362BDY VIS SI4362BDY VIS</p>

heiße Teile

Mehr

SI4336DY-T1-E3	SI4340CDY-T1-E3	SI4340CDY-T1-E3	SI4340CDY-T1-E3-S	SI4340DY
SI4340DY-T1	SI4340DY-T1-E3	SI4340DY-T1-E3	SI4346DY	SI4346DY-T1-E3
SI4346DY-T1-E3	SI4346DY-T1-GE3	SI4346DY-T1-GE3	SI4348DY	SI4348DY-T1-E3
SI4348DY-T1-E3	SI4348DY-T1-GE3	SI4354DY-T1-E3	SI4354DY-T1-E3	SI4355-B1A-FMR
SI4356ADY-T1-E3	SI4356DY	SI4356DY-T1	SI4356DY-T1-E3	SI4362BDY
SI4362BDY-T1-E3	SI4362BDY-T1-E3-PBF	SI4362DY	SI4362DY-T1	SI4362DY-T1-E3
SI4362DY-T1-E3.	SI4364DY	SI4364DY-T1	SI4364DY-T1-E3	SI4366DY-T1-E3
SI4368DY	SI4368DY-T1-E3	SI4368DY-T1-E3	SI4370DY-T1-E3	SI4376DY-T1-E3
SI4378DY-T1	SI4378DY-T1-E3	SI4378DY-T1-E3	SI4382DY-T1-E3	SI4384DY
SI4384DY-T1-E3	SI4384DY-T1-E3	SI4384DY-T1-E3..	SI4386DY	SI4386DY-T1-E3

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